

5.1.2 **RHE MICROSYSTEMS**

The Process Capability Approval (PCA) of the Hybrid Line RHe Microsystems in Radeberg, Germany, has been certified by ESA in accordance with the requirements of ESCC Basic specification No. [2566000](#).

The associated PID includes RHe's manufacturing, assembly and test operations which have been approved for the supply of Hermetic Hybrid products for use in ESA space systems as a Category1, Option 1 Manufacturer, in accordance with ECSS-Q-ST-60-05C Rev.1

5.1.2.1 **Contact Information**

Address	ESCC Chief Inspector
Rhe Microsystems Heidestrasse 70 01454 Radeberg Germany	Mr. Robert Müller Robert.Mueller@cicor.com

5.1.2.2 **Process Capability Approval**

Certificate No.	Certified since:	Type Designation
354	August 2018	Thick Film Hermetic Hybrid Integrated Circuits and HTCC Hermetic Hybrid Integrated Circuits

5.1.2.3 **Capability Abstract**

RHe's hybrid manufacturing line capabilities are defined within the associated Process Identification Document (PID) L7.103 Issue 07.

This specification describes all processes, components/materials and their documentation used by RHe for the production, screening, test and quality control of the following Hybrid types :

- Thick Film Multilayer Hybrid up to 5 conductive layers
- Low /Medium Power, Low-Voltage
- Chip and Wire
- Hermetically sealed Kovar-and Ceramic- Packages.

Processes run on state of the art automated equipment to realize requirements in regard to process capability and volume.

Details to the general Process Capability Domain:

- Substrate information:

Subtechnique	Domain
Substrate Material:	Al2O3
Max No. of screen printed conductor layers:	5
Untrimmed Printed resistors: Min sheet resistance Max sheet resistance	10Ω/sq 1MΩ/sq
Trimmed Printed resistors: Min sheet resistance Max sheet resistance	10Ω/sq 1MΩ/sq

- Assembly Information:

- Substrate attach:

Substrate type	Back metallization	Attached to	Attached by	Inter-connection
Thick film alumina	No	Au plated Kovar	Non-conductive Epoxy	Al / Au wire
Thick film alumina	No	Au plated W/Cu	Non-conductive Epoxy	Al / Au wire
Thick film alumina	No	HTCC	Non-conductive Epoxy	Al / Au wire

- Element attach:

Component type	Material	Top metal.	Bottom metal	Attachment	Inter-connection
passive components:					
Resistor	Si	Al	Si	Non-conductive Epoxy	Al wire
Capacitor	Multilayer ceramic	N/A	AgPd	Conductive + Non-conductive epoxy	Conductive epoxy
active components:					
IC	Si	Al	Si	conductive epoxy	Al / Au wire
Transistor	Si	Al	Au	conductive epoxy	Al wire
Transistor	Si	Al	CrNiAg	conductive epoxy	Al wire
Transistor	Si	Al	Ti/Ni/Au	reflow soldering	Al wire
Diode	Si	Al	Au	conductive epoxy	Al wire
Diode	Si	Al	Ti/Ni/Au	reflow soldering	Al wire

- Encapsulation:

Package type	Material	Sealing by
Metal FP	Kovar	Seam welding

	Au finish	
Metal FP	W/Cu base Kovar frame Au finish	Seam welding
Metal Plug In	Kovar Au finish	Seam welding
Ceramic Quad Flat Package (CQFJ)	HTCC base Kovar frame Au finish	Seam welding

- Screening / LAT information:

Screening as well as Lot acceptance testing is performed according to the PID in conformance to the generic procurement specification ECSS-Q-ST-60-05C Rev.1.